

HRS75N07V

70V N-Channel Trench MOSFET

FEATURES

- ❑ Originative New Design
- ❑ Superior Avalanche Rugged Technology
- ❑ Excellent Switching Characteristics
- ❑ Unrivalled Gate Charge : 80 nC (Typ.)
- ❑ Extended Safe Operating Area
- ❑ Lower $R_{DS(ON)}$: 6.0 m Ω (Typ.) @ $V_{GS}=10V$
- ❑ 100% Avalanche Tested

$$BV_{DSS} = 70 V$$

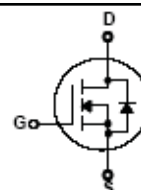
$$R_{DS(on) typ} = 6 m\Omega$$

$$I_D = 48 A$$

TO-220F



1.Gate 2. Drain 3. Source



Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	70	V
I_D	Drain Current – Continuous ($T_C = 25^\circ C$)	48 *	A
	Drain Current – Continuous ($T_C = 100^\circ C$)	30 *	A
I_{DM}	Drain Current – Pulsed (Note 1)	192 *	A
V_{GS}	Gate-Source Voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	810	mJ
I_{AR}	Avalanche Current (Note 1)	48	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	4.8	mJ
dv/dt	Peak Diode Recovery dv/dt	15	V/ns
P_D	Power Dissipation ($T_C = 25^\circ C$) - Derate above $25^\circ C$	38	W
		0.3	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ C$

* Drain current limited by maximum junction temperature

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	3.3	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Electrical Characteristics $T_J=25\text{ }^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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On Characteristics

V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\ \text{V}, I_D = 24\ \text{A}$	--	6.0	7.5	m Ω

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\ \text{V}, I_D = 250\ \mu\text{A}$	70	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 70\ \text{V}, V_{GS} = 0\ \text{V}$	--	--	1	μA
		$V_{DS} = 56\ \text{V}, T_J = 125\text{ }^\circ\text{C}$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20\ \text{V}, V_{DS} = 0\ \text{V}$	--	--	± 100	nA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\ \text{V}, V_{GS} = 0\ \text{V},$ $f = 1.0\ \text{MHz}$	--	4000	5200	pF
C_{oss}	Output Capacitance		--	350	455	pF
C_{rss}	Reverse Transfer Capacitance		--	250	325	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 35\ \text{V}, I_D = 40\ \text{A},$ $R_G = 25\ \Omega$	--	75	160	ns	
t_r	Turn-On Rise Time		--	150	310	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4,5)	--	150	310	ns
t_f	Turn-Off Fall Time			--	60	130	ns
Q_g	Total Gate Charge	$V_{DS} = 56\ \text{V}, I_D = 40\ \text{A},$ $V_{GS} = 10\ \text{V}$	--	80	105	nC	
Q_{gs}	Gate-Source Charge		(Note 3,4)	--	20	--	nC
Q_{gd}	Gate-Drain Charge			--	30	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I_S	Continuous Source-Drain Diode Forward Current	--	--	48	A	
I_{SM}	Pulsed Source-Drain Diode Forward Current	--	--	192		
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 48\ \text{A}, V_{GS} = 0\ \text{V}$	--	--	1.2	V
t_{rr}	Reverse Recovery Time	$I_S = 48\ \text{A}, V_{GS} = 0\ \text{V}$ $di_F/dt = 100\ \text{A}/\mu\text{s}$ (Note 3)	--	80	--	ns
Q_{rr}	Reverse Recovery Charge		--	180	--	nC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L=450\ \mu\text{H}, I_{AS}=48\ \text{A}, V_{DD}=25\ \text{V}, R_G=25\ \Omega,$ Starting $T_J=25\text{ }^\circ\text{C}$
3. $I_{SD}\leq 48\ \text{A}, di/dt\leq 100\ \text{A}/\mu\text{s}, V_{DD}\leq BV_{DSS},$ Starting $T_J=25\text{ }^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\ \mu\text{s},$ Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature

Typical Characteristics

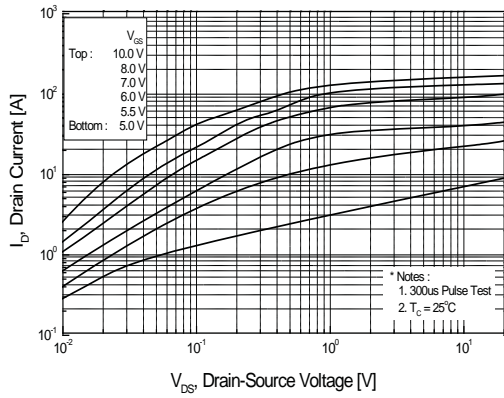


Figure 1. On Region Characteristics

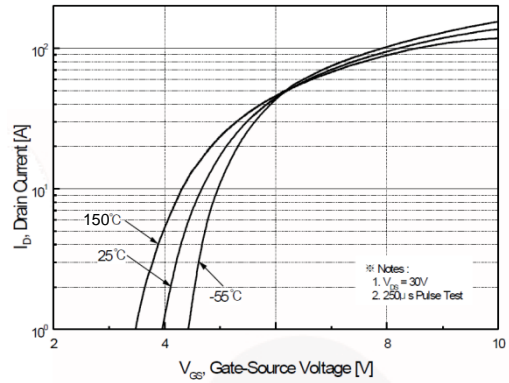


Figure 2. Transfer Characteristics

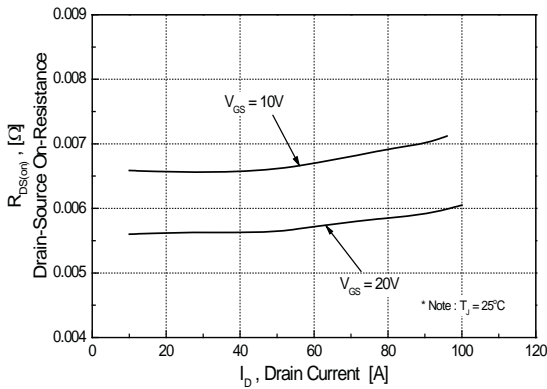


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

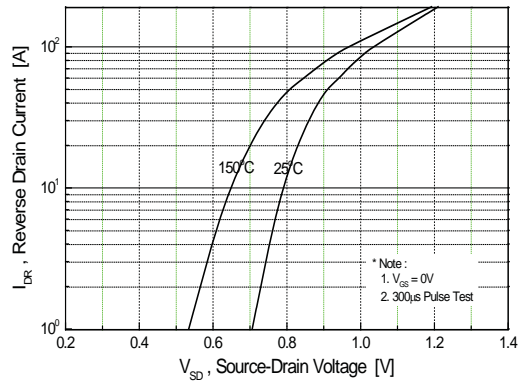


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

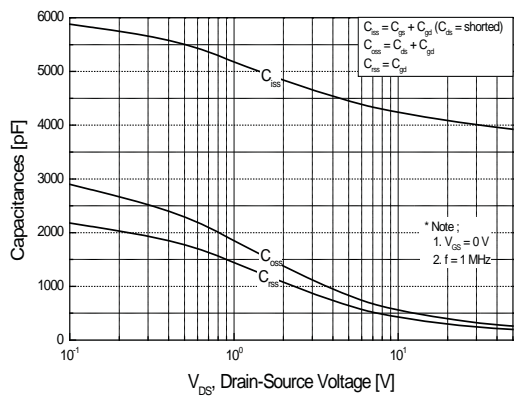


Figure 5. Capacitance Characteristics

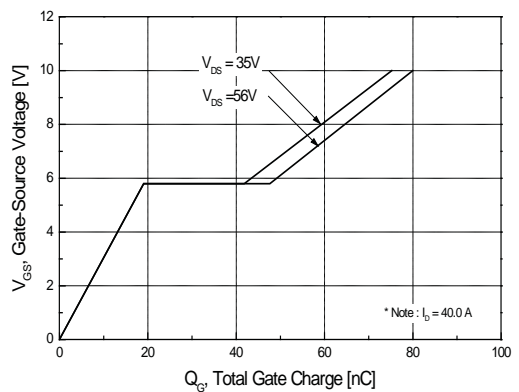


Figure 6. Gate Charge Characteristics

Typical Characteristics

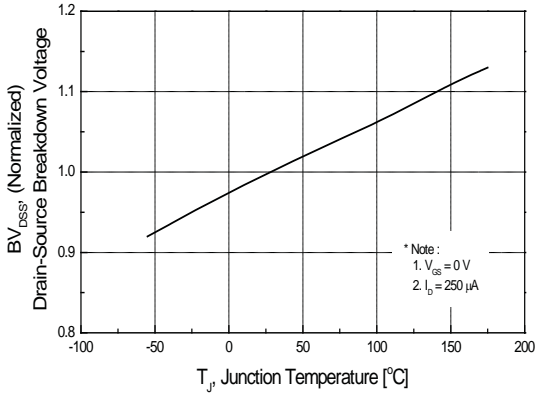


Figure 7. Breakdown Voltage Variation vs Temperature

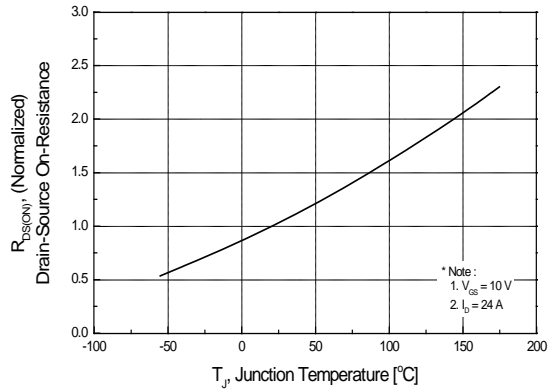


Figure 8. On-Resistance Variation vs Temperature

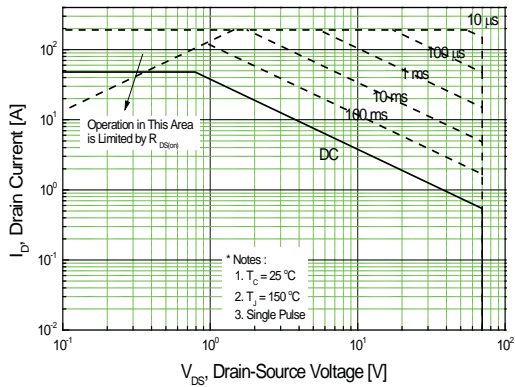


Figure 9. Maximum Safe Operating Area

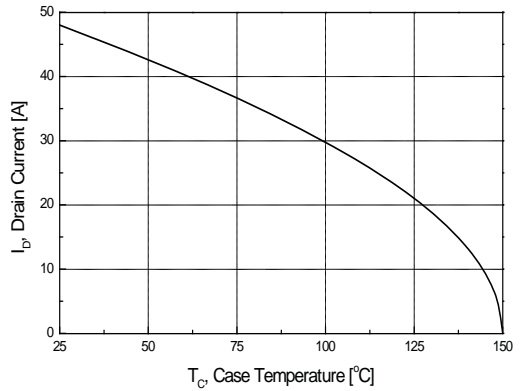


Figure 10. Maximum Drain Current vs Case Temperature

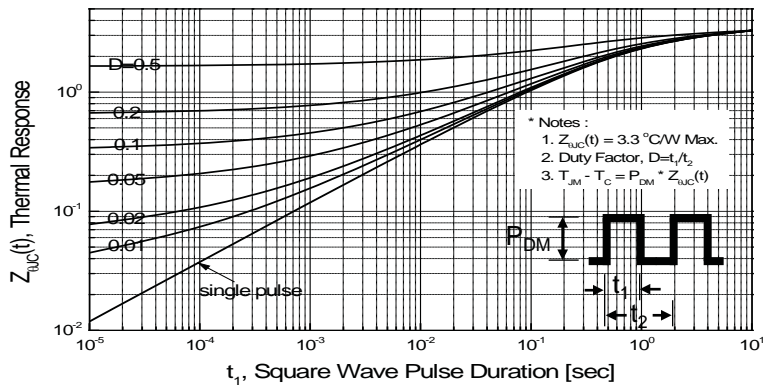


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform



Fig 13. Resistive Switching Test Circuit & Waveforms

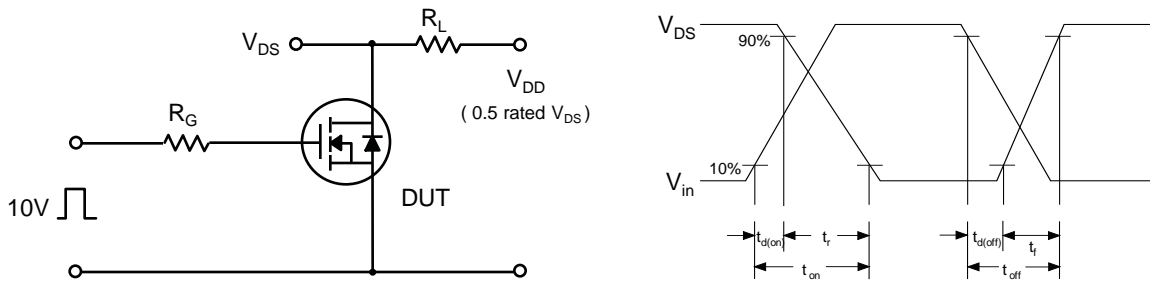


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

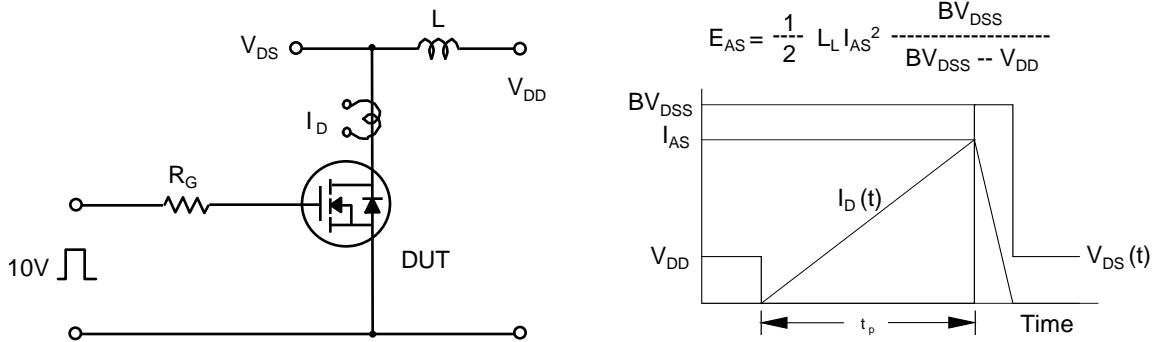
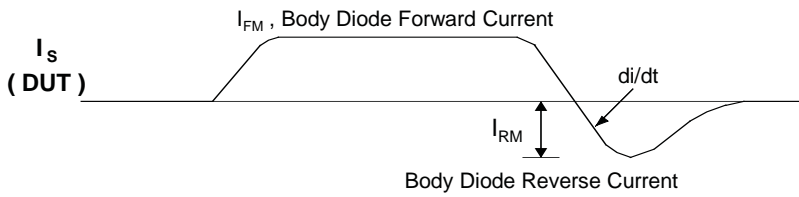


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

TO-220F

